128K-BIT CMOS MASK ROM



The LC3100 is a 128K-bit CMOS mask ROM that contains an interface connectable direct to the speech synthesizer LSI LC8100. With one piece of this mask ROM, approximately 100 seconds of speech synthesis can be attained.

A selection of 8-bit, 4-bit, or single-bit output data is allowed by means of external control. This mask ROM is also suited for use in applications other than speech synthesis.

Features

- ROM capacity: 128K bits
- Access time:

6.9 µsec typ (for operation at 800kHz typ.) 25.6 µsec typ (for operation at 200kHz typ.)

- Cycle time:
 - 8.1 μ sec typ (for operation at 800kHz typ.) 30.6 μ sec typ (for operation at 200kHz typ.)
- Function:
 - Contains an interface to the LC8100 (speech synthesizer LSI).

Possible to select the bit length of output data.

8-bit data

4-bit data Single-bit data

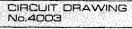
- Low power dissipation: CMOS
- Current dissipation:

2mA max. (at operating mode) 1μA max. (at nonoperating mode)

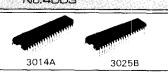
- Single +5V power supply: +2.7 to 6.0V (supply voltage range)
- Package: DIP 24

LC3101

c-mos LSI



128K-BIT CMOS MASK ROM



The LC3101 is a 128k-bit CMOS mask ROM that contains an interface connectable direct to the speech synthesizer LSI LC8100. With one piece of this mask ROM, approximately 100 seconds of speech synthesis can be attained. Since it also contains an interface connectable direct to an EPROM, speech synthesis can be attained by using this mask ROM and an EPROM jointly.

A selection of 8-bit, 4-bit, or single-bit output data is allowed by means of external control. This mask ROM is also suited for use in applications other than speech synthesis.

Features

ROM capacity

128K bits

Access time

25.6µsec typ (for operation at 200kHz typ.)

Cycle time

30.6µsec typ (for operation at 200kHz typ.)

■ Function

· Contains an interface to an EPROM.

- Contains an interface to the LC8100 (speech synthesizer LSI).
- · Possible to select the bit length of output data.

8-bit data

4-bit data

Single-bit data

Low power dissipation

CMOS

■ Current dissipation

2mA max. (at operating mode)

 $1\mu A$ max. (at nonoperating mode)

■ Single +5V power supply

+2.7 to 6.0V (supply voltage range)

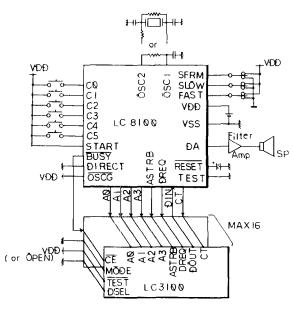
■ Package

DIP24

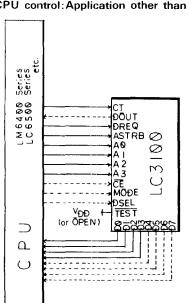


4001:LC3100 SAMPLE APPLICATION CIRCUIT (1)

One word to one key correspondence

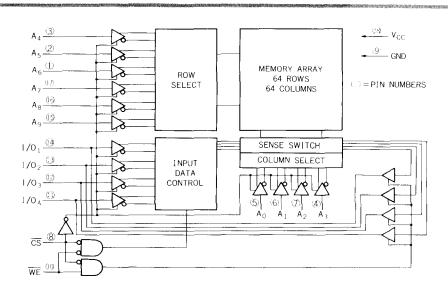


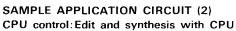
SAMPLE APPLICATION CIRCUIT (3) CPU control:Application other than speech synthesis

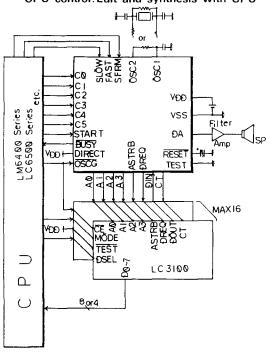


Note) Connect signals shown with dotted lines as required.

4002:LC3514,3514D,E,L BLOCK DIAGRAM









Continued from preceding page.

●8 BITS, SINGLE CHIP (N-MOS INTEGRATED CIRCUIT)

Type Number	Page		Case		Circuit	Applications	ROM	RAM	Stacks	Cycle Time	IDO	Po	ort	Remarks
Type Number	Tage	Package	Pins	Package No.	Drawing No.	Applications	(Bytes)	(Bits)	Stacks	(µs)	(mA)	Max. Voltage (V)	Max. Current (mA)	Veningres
* L M 8 8 5 2 * L M 8 8 0 2	89 89	DIP DIP	64S 42S	- 3025B		<u> </u>	2K 2K	128×8 128×8	16 16	1 1	60 60	15 15	20 20	

SPEECH SYNTHESIS APPLICATIONS (monolithic integrated circuit)

T N	<u> </u>		Case		C::					
Type Number	Page	Package	Pins	Package No.	Circuit Drawing No.	Circuit Functions & Applications	Main Specifications			
L C 8 1 0 0	243	DIP	28	3012A	4111	PARCOR System-Applied 1-Chip Speech Synthesizer	Male & female voices, speech duration approx. 20sec, automatic power-on/down function			
L C 3 1 0 0	203	DIP	24	3011A	4001	128K-Bit CMOS Mask ROM Externally Connected to LC8100	Contains interface to LC8100.approx. 100secof speech synthes is with 1 pc. of this ROM			
L C 3 1 0 1	203	DIP	42 42S	3014A 3025B	4003	128K-Bit CMOS Mask ROM Externally Connected to LC8100	Contains interface to LC8100 and E-PROM interface. speech duraation approx, 100 sec.			
OLA6805M	148	MFP	14	3034A	2116	Audio Amp for Speech Synthesis	MFP version of LA6805			

MEMORIES (monolithic integrated circuit)

Type Number	Door		Case		C:i.		
	Page	Package	Pins	Package No.	Circuit Drawing No.	Circuit Functions & Applications	Main Specifications
LC3100	203	DIP	24	3011A	4001	128K Mask ROM	ROM dedicated to speech synthesis
		Į	İ		ĺ		(See description of speech synthesis LSI.)
LC3101	203	DIP	42	3014A	4003	128K Mask ROM	ROM dedicated to speech synthesis
	ĺ	DIP	42S	3025B	Ì		(See description of speech synthesis LSI.)
LC3514	204	DIP	18	3007A)	C-MOS 4K Static RAM (1K×4bits)	High speed, pin compatible with 2114(Nch)
LC3514D	204	DIP	18	3007A	4002	C-MOS 4K Static RAM (1K×4bits)	Wide oprating voltage range low standby current, pin compatible with
				1			2114
LC3514E	204	DIP	18	3007A	4002	C-MOS 4K Static RAM (1K×4bits)	Wide operating voltage range, pin compatible with 2114
LC3514L	204	DIP	18	3007A		C-MOS 4K Static RAM (1K×4bits)	High speed, low standby current, pin compatible with 2114
DLC3516	205	DIP	24	3011A	4004	C-MOS 16K Static RAM (2K×8bits)	High speed, low standby current, pin compatible with 2716 (EPROM)

Continued from preceding page.

●8 BITS, SINGLE CHIP (N-MOS INTEGRATED CIRCUIT)

Type Number	Page		Case		Circuit	Applications	ROM	RAM	Stacks	Cycle Time	IDO	Po	ort	Remarks
Type Number	Tage	Package	Pins	Package No.	Drawing No.	Applications	(Bytes)	(Bits)	Stacks	(µs)	(mA)	Max. Voltage (V)	Max. Current (mA)	Veningres
* L M 8 8 5 2 * L M 8 8 0 2	89 89	DIP DIP	64S 42S	- 3025B		<u> </u>	2K 2K	128×8 128×8	16 16	1 1	60 60	15 15	20 20	

SPEECH SYNTHESIS APPLICATIONS (monolithic integrated circuit)

T N	<u> </u>		Case		C::					
Type Number	Page	Package	Pins	Package No.	Circuit Drawing No.	Circuit Functions & Applications	Main Specifications			
L C 8 1 0 0	243	DIP	28	3012A	4111	PARCOR System-Applied 1-Chip Speech Synthesizer	Male & female voices, speech duration approx. 20sec, automatic power-on/down function			
L C 3 1 0 0	203	DIP	24	3011A	4001	128K-Bit CMOS Mask ROM Externally Connected to LC8100	Contains interface to LC8100.approx. 100secof speech synthes is with 1 pc. of this ROM			
L C 3 1 0 1	203	DIP	42 42S	3014A 3025B	4003	128K-Bit CMOS Mask ROM Externally Connected to LC8100	Contains interface to LC8100 and E-PROM interface. speech duraation approx, 100 sec.			
OLA6805M	148	MFP	14	3034A	2116	Audio Amp for Speech Synthesis	MFP version of LA6805			

MEMORIES (monolithic integrated circuit)

Type Number	Door		Case		C:i.		
	Page	Package	Pins	Package No.	Circuit Drawing No.	Circuit Functions & Applications	Main Specifications
LC3100	203	DIP	24	3011A	4001	128K Mask ROM	ROM dedicated to speech synthesis
		Į	İ		ĺ		(See description of speech synthesis LSI.)
LC3101	203	DIP	42	3014A	4003	128K Mask ROM	ROM dedicated to speech synthesis
	ĺ	DIP	42S	3025B	Ì		(See description of speech synthesis LSI.)
LC3514	204	DIP	18	3007A)	C-MOS 4K Static RAM (1K×4bits)	High speed, pin compatible with 2114(Nch)
LC3514D	204	DIP	18	3007A	4002	C-MOS 4K Static RAM (1K×4bits)	Wide oprating voltage range low standby current, pin compatible with
				1			2114
LC3514E	204	DIP	18	3007A	4002	C-MOS 4K Static RAM (1K×4bits)	Wide operating voltage range, pin compatible with 2114
LC3514L	204	DIP	18	3007A		C-MOS 4K Static RAM (1K×4bits)	High speed, low standby current, pin compatible with 2114
DLC3516	205	DIP	24	3011A	4004	C-MOS 16K Static RAM (2K×8bits)	High speed, low standby current, pin compatible with 2716 (EPROM)